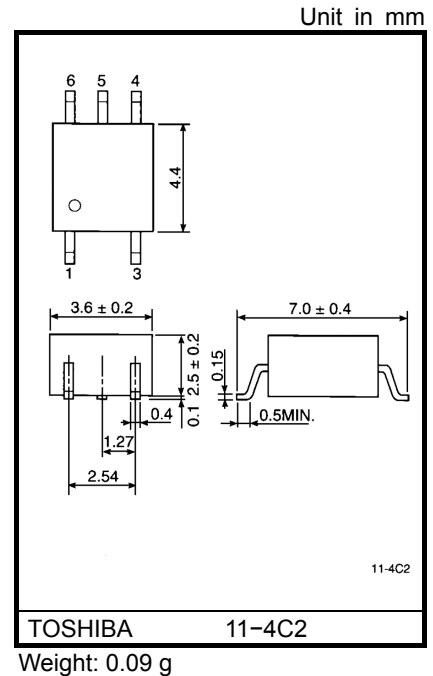


TLP115

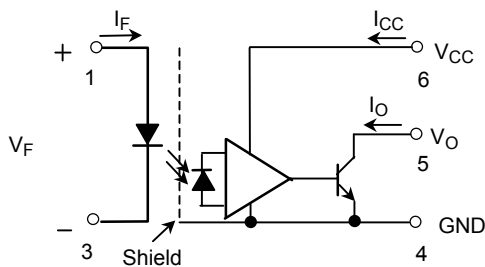
High Speed, Long Distance Isolated Line Receiver
 Microprocessor System Interfaces
 Digital Isolation For A / D, D / A Conversion
 Computer-Peripheral Interfaces
 Ground Loop Elimination

The TOSHIBA mini flat coupler TLP115 is small outline coupler, suitable for surface mount assembly.
 TLP115 consists of a GaAlAs light emitting diode, optically coupled to an integrated high gain, high speed shielded photo detector whose output is an open collector schottky clamped transistor.
 The shield, which shunts capacitively coupled common noise to ground, provides a guaranteed transient immunity specification of 1000V / μ s.

- Input current thresholds: $I_F=10\text{mA}$ (max.)
- Switching speed: 10MBd (typ.)
- Common mode transient immunity: $\pm 1000\text{V} / \mu\text{s}$ (min.)
- Guaranteed performance over temp.: 0~70°C
- Isolation voltage: 2500Vrms (min.)
- UL recognized: UL1577, file no. E67349

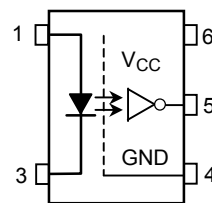


Schematic



Note. A 0.1 μ F bypass capacitor must be connected between pins 4 and 6.

Pin Configuration(top view)



- 1 : Anode
- 3 : Cathode
- 4 : GND
- 5 : V_O (Output)
- 6 : V_{CC}

Truth Table(positive logic)

Input	Output
H	L
L	H

Absolute Maximum Ratings (Ta = 25°C)

Characteristic		Symbol	Rating	Unit
LED	Forward current	I_F	20	mA
	Pulse forward current (Note 1)	I_{FP}	40	mA
	Peak transient forward current (Note 2)	I_{FPT}	1	A
	Reverse voltage	V_R	5	V
Detector	Output current	I_O	25	mA
	Output voltage	V_O	7	V
	Supply voltage (1 minute maximum)	V_{CC}	7	V
	Output power dissipation	P_o	40	mW
Operating temperature range		T_{opr}	-40~85	°C
Storage temperature range		T_{stg}	-55~125	°C
Lead solder temperature(10s)		T_{sol}	260	°C
Isolation voltage (AC, 1min., RH ≤ 60%, Note 4)		BV_S	2500	Vrms

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

(Note 1) 50% duty cycle, 1ms pulse width.

(Note 2) Pulse width ≤ 1μs, 300pps.

Recommended Operating Conditions

Characteristic	Symbol	Min.	Typ.	Max.	Unit
Input voltage, low level	V_{FL}	-3	0	1.0	V
Input current, high level	I_{FH}	13	16	20	mA
Supply voltage	V_{CC}	4.5	5	5.5	V
Fan out (TTL load, each channel)	N	—	—	8	—
Operating temperature	T_{opr}	0	—	70	°C

Note: Recommended operating conditions are given as a design guideline to obtain expected performance of the device. Additionally, each item is an independent guideline respectively. In developing designs using this product, please confirm specified characteristics shown in this document.

Electrical Characteristics

(unless otherwise specified, $T_a = 0\sim 70^\circ\text{C}$, $V_{CC} = 4.5\sim 5.5\text{V}$, $V_{FL} \leq 1.0\text{V}$)

Characteristic	Symbol	Test Condition	Min.	Typ.*	Max.	Unit
Forward voltage	V_F	$I_F=10\text{mA}$, $T_a=25^\circ\text{C}$	—	1.65	1.80	V
Forward voltage temperature coefficient	V_F / T_a	$I_F=10\text{mA}$	—	-2	—	mV / °C
Reverse current	I_R	$V_R=5\text{V}$, $T_a=25^\circ\text{C}$	—	—	10	μA
Capacitance between terminals	C_T	$V_F=0$, $f=1\text{MHz}$, $T_a=25^\circ\text{C}$	—	45	—	pF
High level output current	I_{OH}	$V_F=1.0$, $V_O=5.5\text{V}$	—	—	250	μA
		$V_F=1.0$, $V_O=5.5\text{V}$, $T_a=25^\circ\text{C}$	—	0.5	10	
Low level output voltage	V_{OL}	$I_F=10\text{mA}$ $I_{OL}=13\text{mA}(\text{sinking})$	—	0.4	0.6	V
"H level output → L level output" input current	I_{FH}	$I_{OL}=13\text{mA}(\text{sinking})$ $V_{OL}=0.6\text{V}$	—	—	10	mA
High level supply current	I_{CCH}	$V_{CC}=5.5\text{V}$, $I_F=0$	—	7	15	mA
Low level supply current	I_{CCL}	$V_{CC}=5.5\text{V}$, $I_F=16\text{mA}$	—	12	18	mA
Input-output insulation leakage current	I_S	$V_S=3540\text{V}$, $t=5\text{s}$ $T_a=25^\circ\text{C}$ (Note 4)	—	—	100	μA
Isolation resistance	R_S	R.H. $\leq 60\%$, $V_S=500\text{V DC}$ $T_a=25^\circ\text{C}$ (Note 4)	5×10^{10}	10^{14}	—	Ω
Stray capacitance between input to output	C_S	$V_S=0$, $f=1\text{MHz}$ $T_a=25^\circ\text{C}$ (Note 4)	—	0.8	—	pF

* All typical values are $V_{CC}=5\text{V}$, $T_a=25^\circ\text{C}$

Switching Characteristics($V_{CC} = 5V$, $T_a = 25^{\circ}C$)

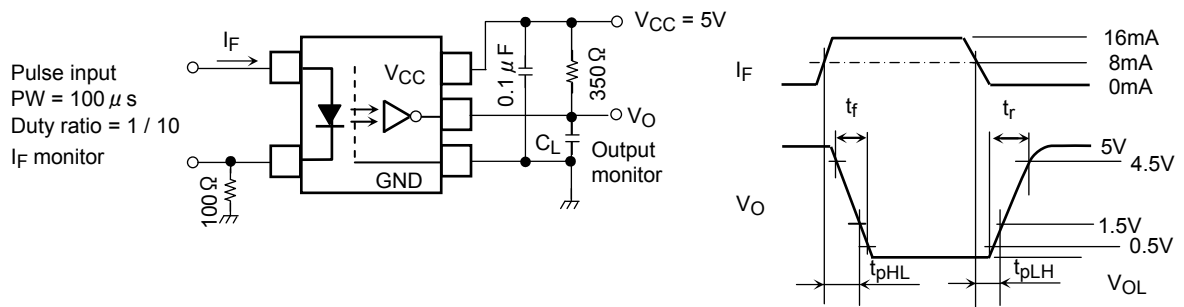
Characteristic	Symbol	Test Circuit	Test Condition	Min.	Typ.	Max.	Unit
Propagation delay time (H→L)	t_{pHL}	1	$I_F=0 \rightarrow 16mA$ $C_L=15pF$, $R_L=350\Omega$	—	60	120	ns
Propagation delay time (L→H)	t_{pLH}	1	$I_F=16 \rightarrow 0mA$ $C_L=15pF$, $R_L=350\Omega$	—	60	120	ns
Output rise fall time (10–90%)	t_r , t_f	2	$R_L=350\Omega$, $C_L=15pF$ $I_F=0 \rightleftarrows 16mA$	—	30	—	ns
Common mode transient immunity at high output level	CM_H	2	$I_F=0mA$, $V_{CM}=400V_{p-p}$ $V_{O(min)}=2V$, $R_L=350\Omega$	1000	—	—	V / μs
Common mode transient immunity at low output level	CM_L	2	$I_F=16mA$, $V_{CM}=400V_{p-p}$ $V_{O(max)}=0.8V$, $R_L=350\Omega$	–1000	—	—	V / μs

(Note 4) Device considered a two-terminal device: Pins 1 and 3 shorted together, and pins 4, 5 and 6 shorted together.

(Note 5) The V_{CC} supply voltage to each TLP115 isolator must be bypassed by 0.1 μF capacitor. This can be either a ceramic or solid tantalum capacitor with good high frequency characteristic and should be connected as close as possible to package V_{CC} and GND pins of each device.

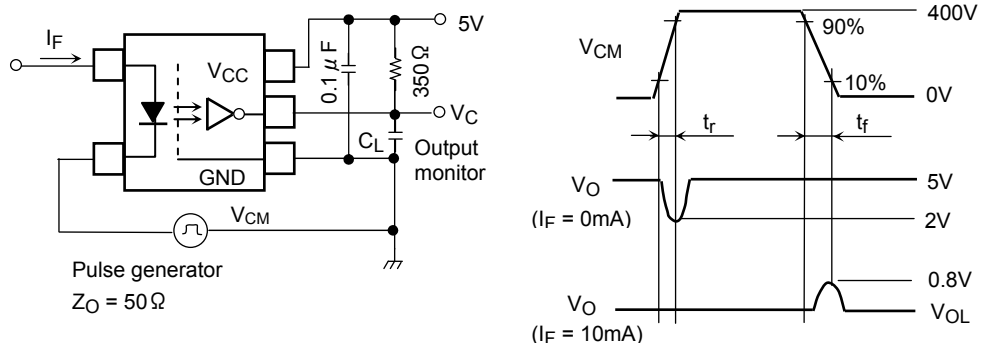
(Note 6) Maximum electrostatic discharge voltage for any pins: 180V(C=200pF, R=0)

Test Circuit 1: Switching Time Test Circuit



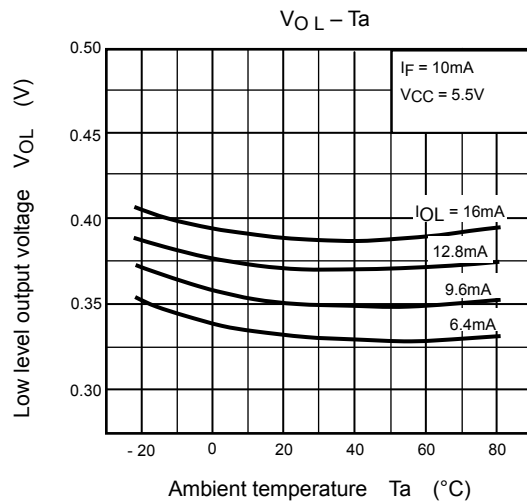
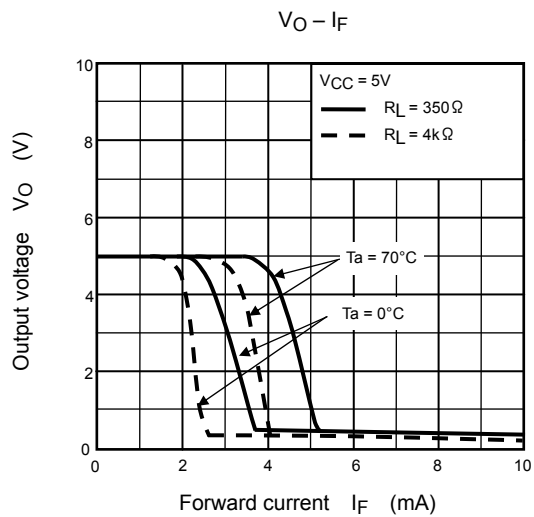
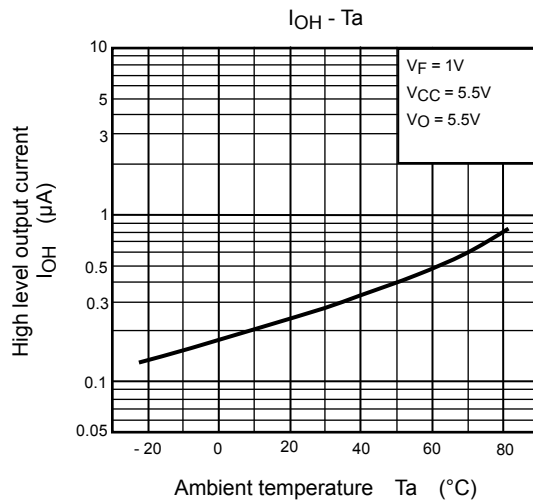
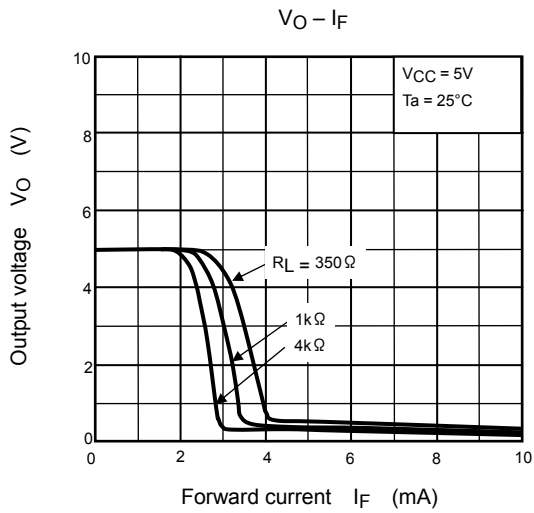
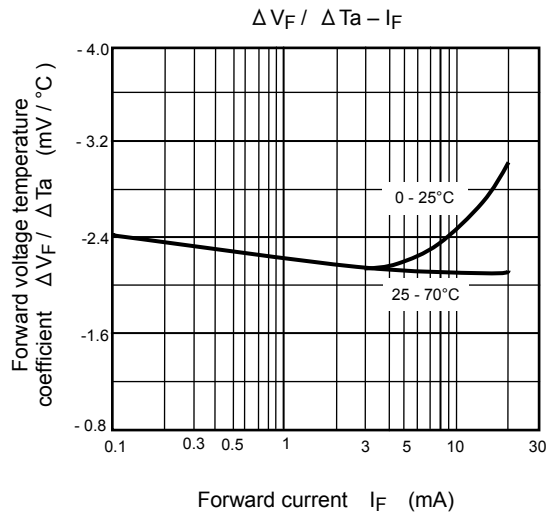
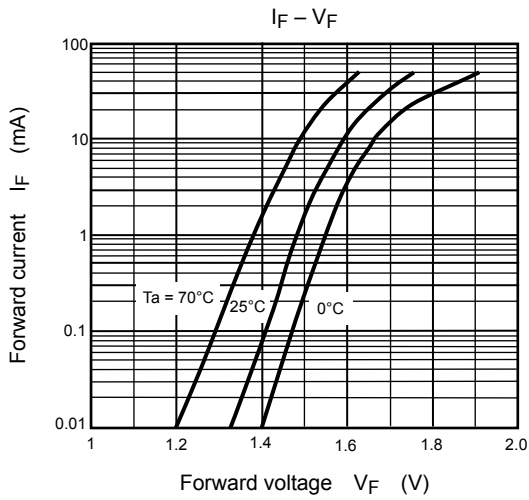
CL is approximately 15pF which includes probe and stray wiring capacitance.

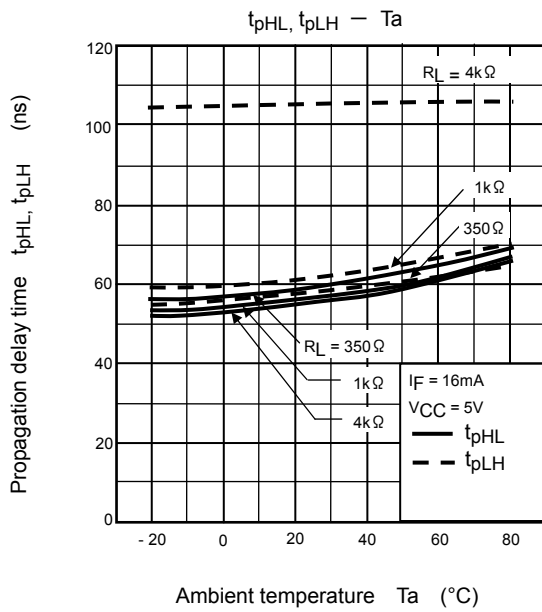
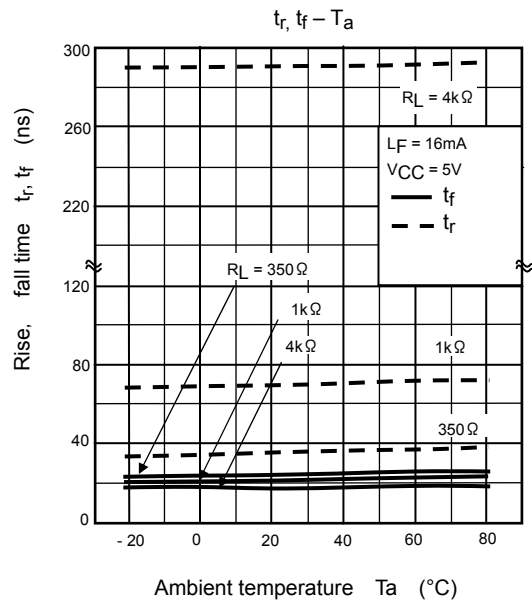
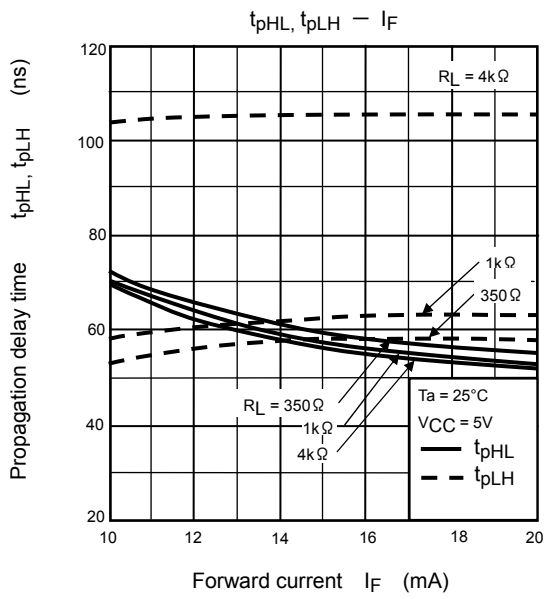
Test Circuit 2: Common Mode Transient Immunity Test Circuit



$$CM_H = \frac{320(V)}{t_r(\mu s)}, CM_L = \frac{320(V)}{t_f(\mu s)}$$

CL is approximately 15pF which includes probe and stray wiring capacitance.





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20070701-EN

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